

# KSH13009A

## KSH13009AF / KSH13009AL

*NPN Silicon Power Transistor, VCBO= 700V, VCEO= 400V, IC= 12A*

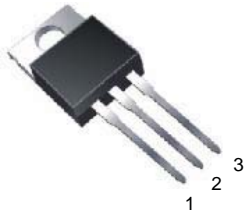
### General Description

- High voltage, high speed power switching
- Suitable for switching regulator, inverters motor controls

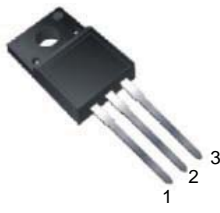
### Features

- VCBO = 700V
- VCEO = 400V
- VBEO = 9V
- IC = 12A

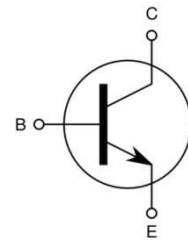
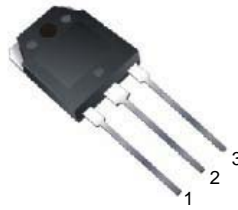
**TO-220**



**TO-220F**



**TO-3P**



### Ordering Information

Ordering number	Package	Pin Assignment			Packing
		1	2	3	
KSH13009A	TO-220	B	C	E	Tube
KSH13009AF	TO-220F	B	C	E	Tube
KSH13009AL	TO-3P	B	C	E	Tube

### h<sub>FE</sub> Classification

Classification	R	O	Y
h <sub>FE</sub>	8 ~ 17	15 ~ 28	26 ~ 39

\* Test Condition : V<sub>CE</sub>=5V, I<sub>C</sub>=5A

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## KSH13009AF / KSH13009AL

*NPN Silicon Power Transistor, VCBO= 700V, VCEO= 400V, IC= 12A*

### Absolute Maximum Ratings TC=25°C unless otherwise noted

CHARACTERISTICS	SYMBOL	RATING			UNIT
		TO-220	TO-220F	TO-3P	
Collector-Base Voltage	$V_{CBO}$	700			V
Collector-Emitter Voltage	$V_{CEO}$	400			V
Emitter-Base Voltage	$V_{EBO}$	9			V
Collector Current(DC)	$I_C$	12			A
Collector Current(Pulse)	$I_{CP}$	24			A
Base Current	$I_B$	6			A
Collector Dissipation(Tc=25°C)	$P_C$	100	50	130	W
Junction Temperature	$T_J$	150			°C
Storage Temperature	$T_{STG}$	-65~150			°C

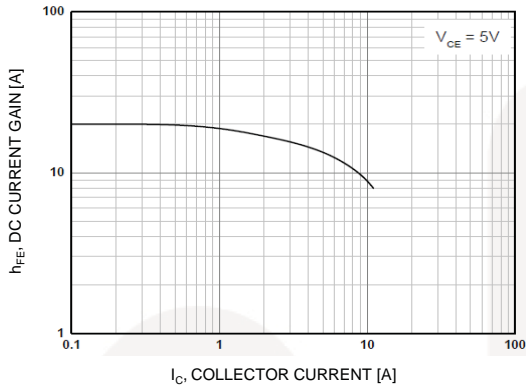
### Electrical Characteristics <sup>(1)</sup> TC=25°C unless otherwise noted

CHARACTERISTICS	SYMBOL	Test Condition	Min	Typ.	Max	Unit
Collector-Base Breakdown Voltage	$V_{CBO}$	$I_C=500\mu A, I_E=0$	700			V
Collector-Emitter Breakdown Voltage	$V_{CEO}$	$I_C=10mA, I_B=0$	400			V
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=9V, I_C=0$			1	mA
DC Current Gain	$h_{FE1}$	$V_{CE}=5V, I_C=5A$	8		40	
	$h_{FE2}$	$V_{CE}=5V, I_C=8A$	6		30	
Collector-Emitter Saturation Voltage	$V_{CE}(sat)$	$I_C=5A, I_B=1A$			1	V
		$I_C=8A, I_B=1.6A$			1.5	V
		$I_C=12A, I_B=3A$			3	V
Base-Emitter Saturation Voltage	$V_{BE}(sat)$	$I_C=5A, I_B=1A$			1.4	V
		$I_C=8A, I_B=1.6A$			1.6	V
Output Capacitance	$C_{ob}$	$V_{CB}=10V, f=0.1MHz$		180		pF
Current Gain Bandwidth Product	$f_T$	$V_{CE}=10V, I_C=0.5A$	4			MHz
Turn on Time	$t_{on}$	$V_{CC}=125V, I_C=8A$ $I_{B1}=1.6A, I_{B2}=-1.6A$ $R_L=15.6\Omega$ (Note 2)			1.1	$\mu s$
Storage Time	$t_{stg}$				3.0	$\mu s$
Fall Time	$t_F$				0.7	$\mu s$

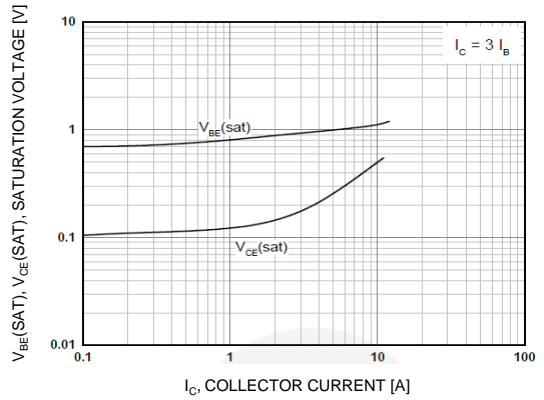
**Notes ;**

- Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 2\%$
- Final Test Condition : UI9600, Vcc=5V, Ic=0.5A (  $t_{stg}$  Class = A : 4.0~4.5, B : 4.5~5.0, C : 5.0~5.5 )

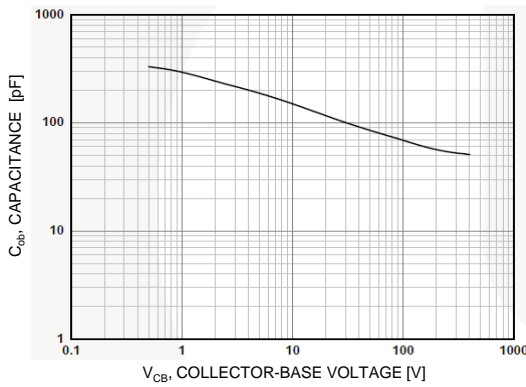
## Typical Characteristics



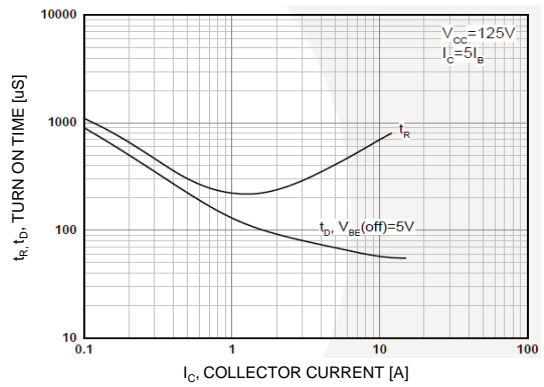
**Figure 1. DC Current Gain**



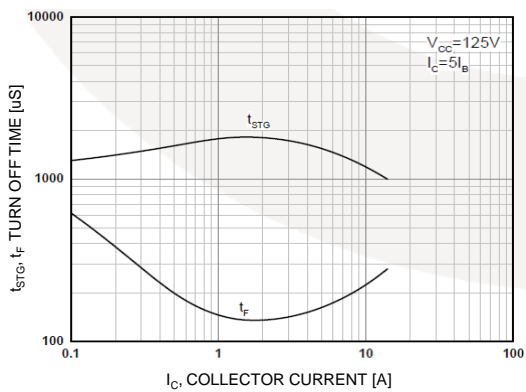
**Figure 2. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage**



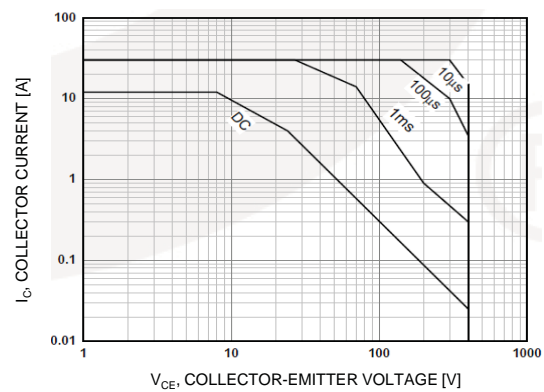
**Figure 3. Collector Output Capacitance**



**Figure 4. Turn On Time**



**Figure 5. Turn Off Time**



**Figure 6. Safe Operating Area**

## Typical Characteristics

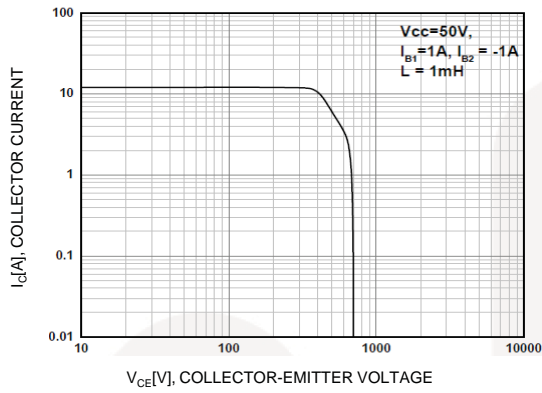


Figure 7. Reverse Biased Safe Operating Area

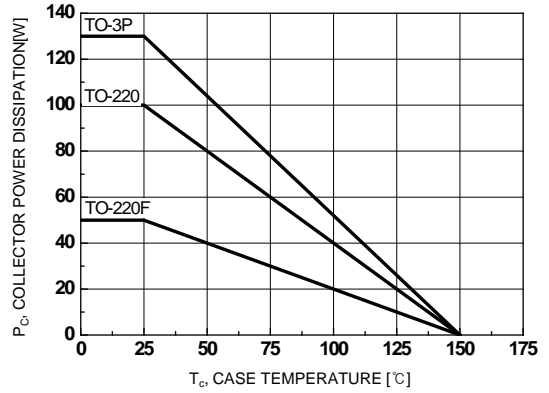
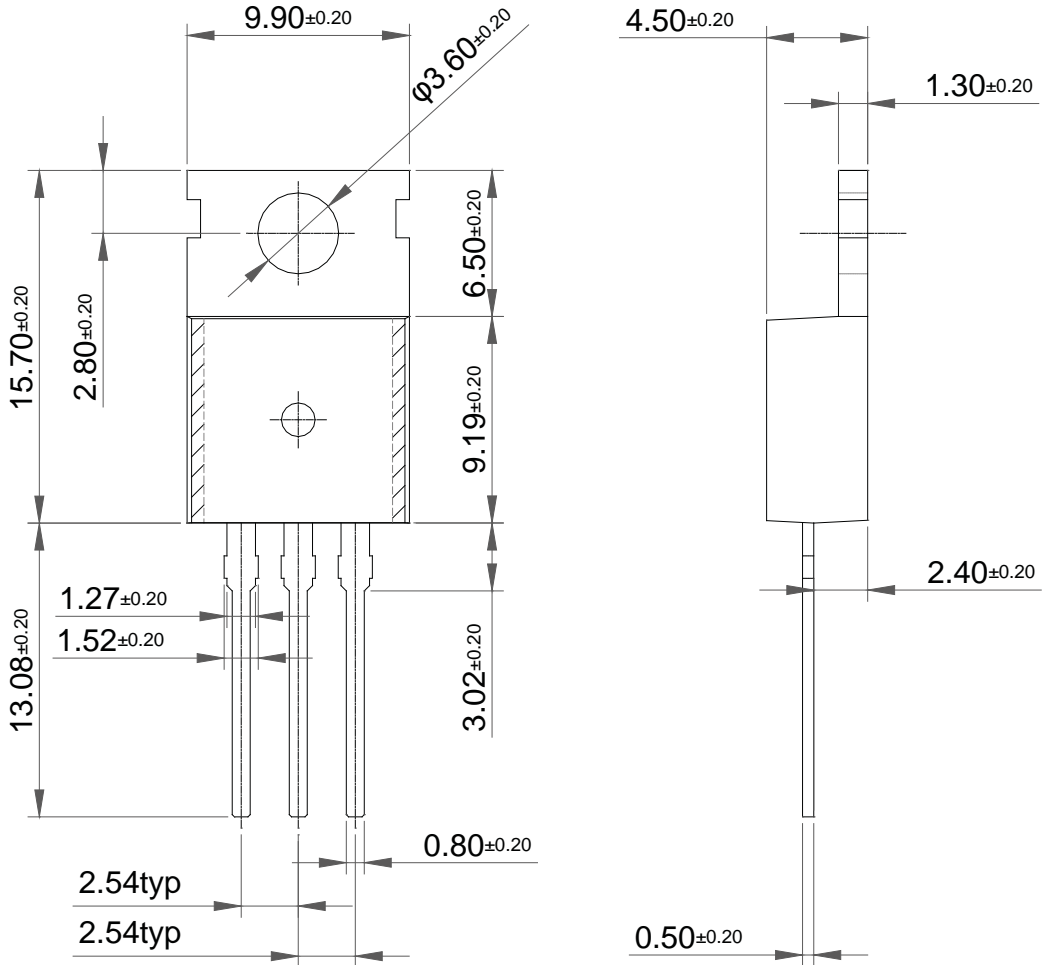


Figure 8. Power Derating

Package Dimension

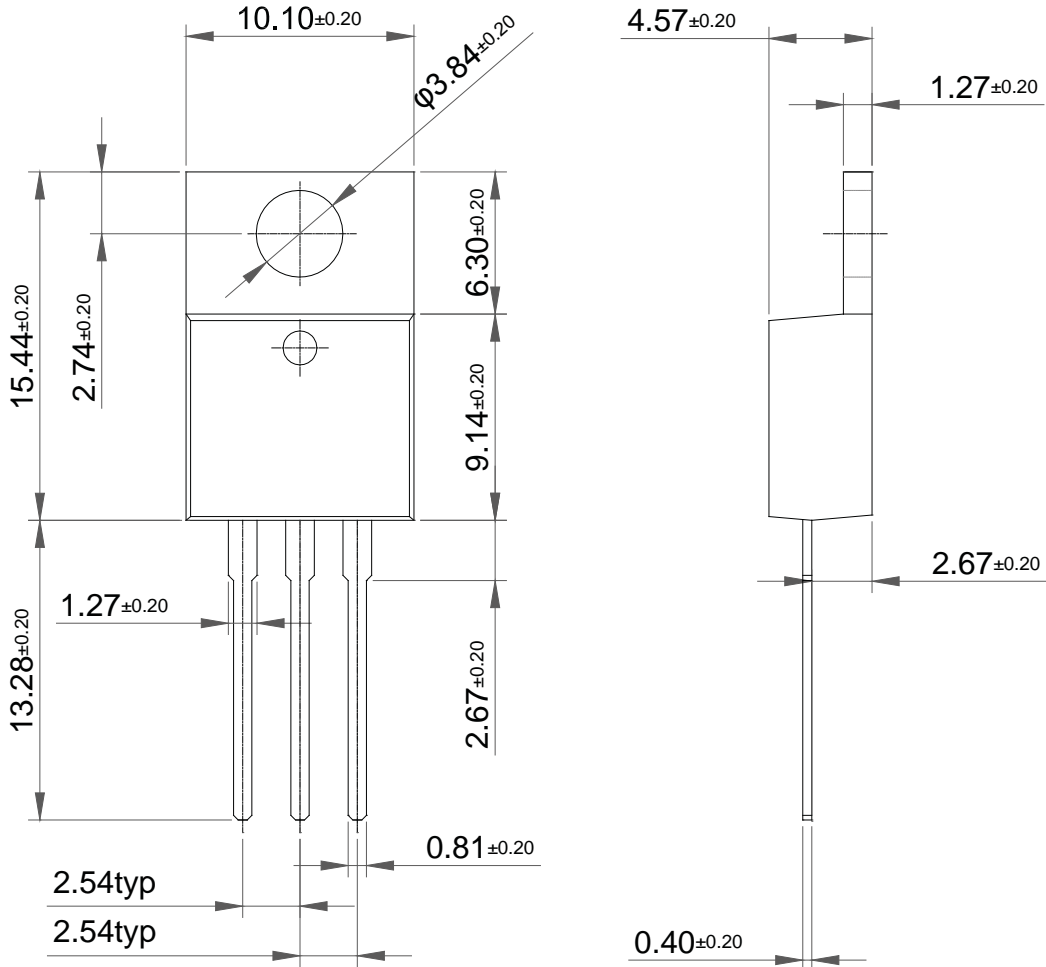
TO-220 (A)



Dimensions in Millimeters

Package Dimension

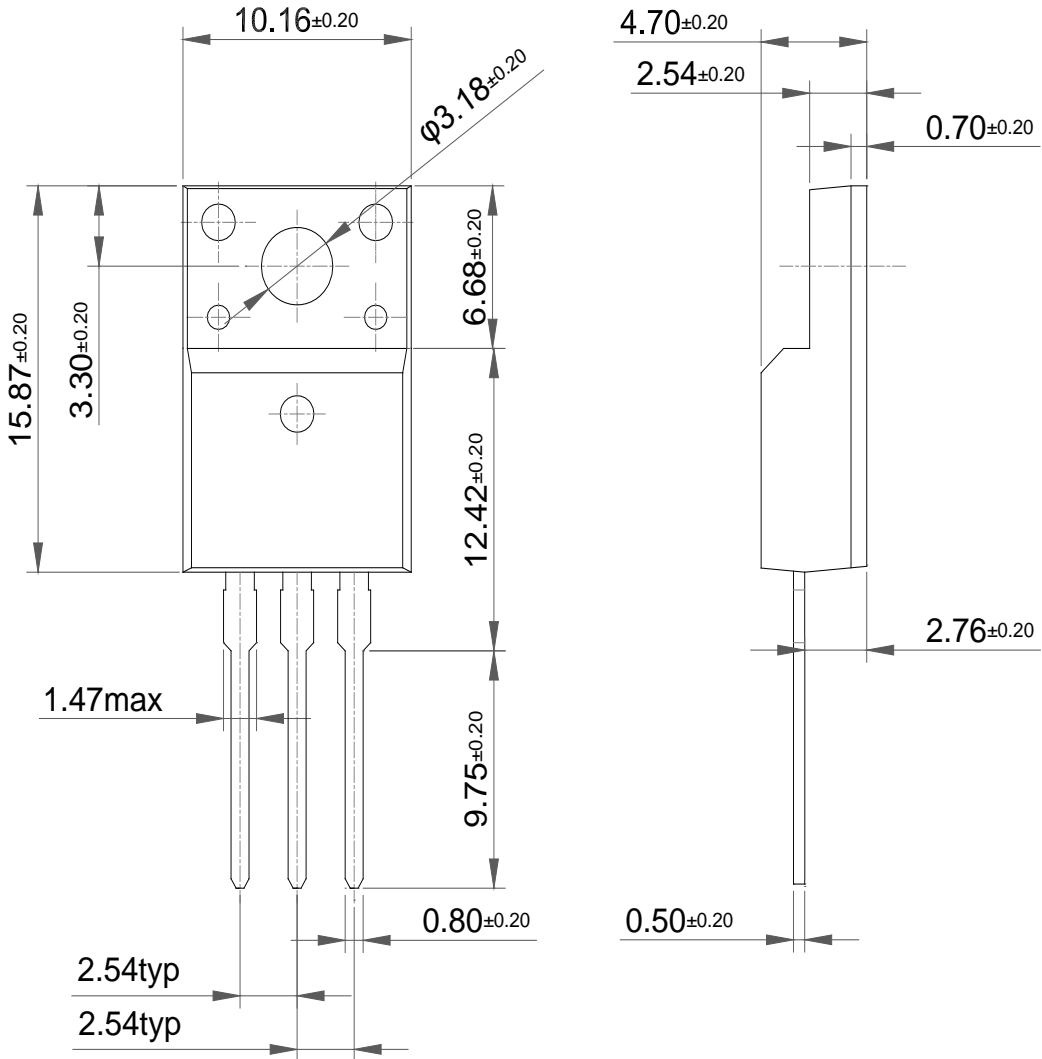
TO-220 (B)



Dimensions in Millimeters

# Package Dimension

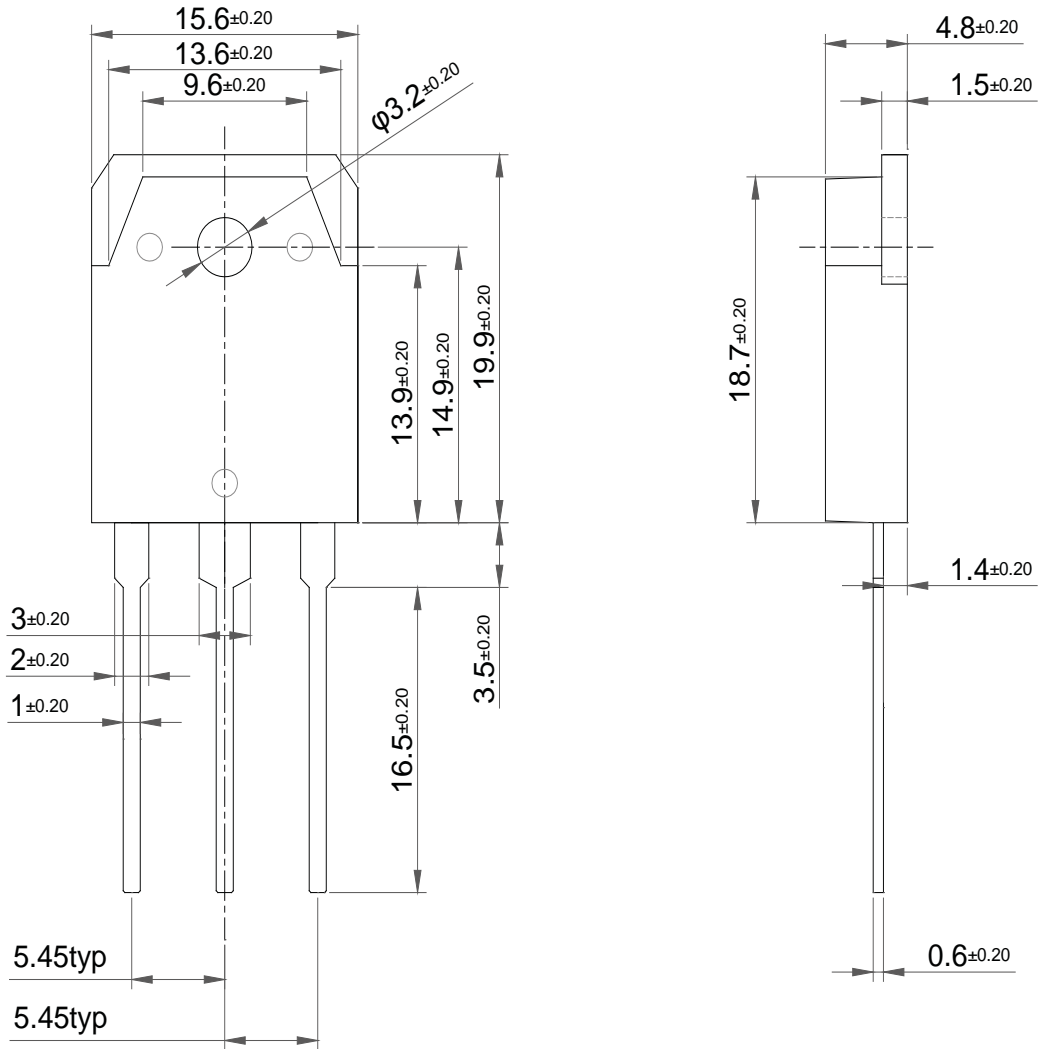
## TO-220F



Dimensions in Millimeters

Package Dimension

TO-3P



Dimensions in Millimeters